

60V N-Channel Enhancement Mode MOSFET

MAIN CHARACTERISTICS

I_D	160A
V_{DS}	60V
R_{DS(on)-typ}(@V_{GS}=10V)	<3mΩ(Typ:2.8mΩ)

FEATURES

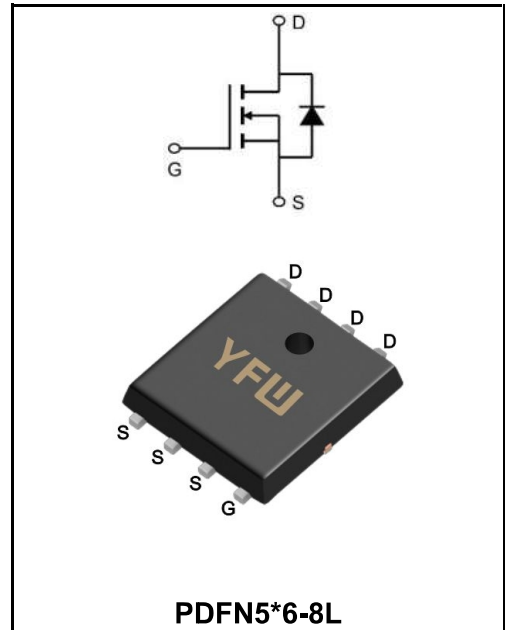
Adopt advanced trench technology to provide excellent Battery protection or in other Switching application.

APPLICATIONS

- ♣ Battery protection
- ♣ Load switch
- ♣ Uninterruptible power supply
- ♣ **YFW-SGT technology**

MECHANICAL DATA

- ♣ Case:PDFN5*6-8L/HNF
- ♣ Mounting Position: Any
- ♣ Molded Plastic: UL Flammability Classification Rating 94V-0
- ♣ Lead free in compliance with EU RoHS 2011/65/EU directive
- ♣ Solder bath temperature 275°C maximum,10s per JESD 22-B106



Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continue Drain Current	I_D	160	A
Pulsed Drain Current (Note1)	I_{DM}	240	A
Power Dissipation	P_D	210	W
Single Pulse Avalanche Energy (Note1)	E_{AS}	650	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	R_{θJC}	0.59	°C/W
Thermal Resistance, Junction to Ambient	R_{θJA}	50	°C/W

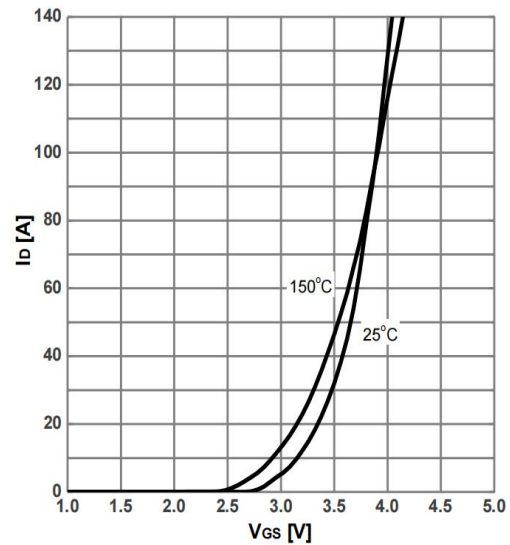
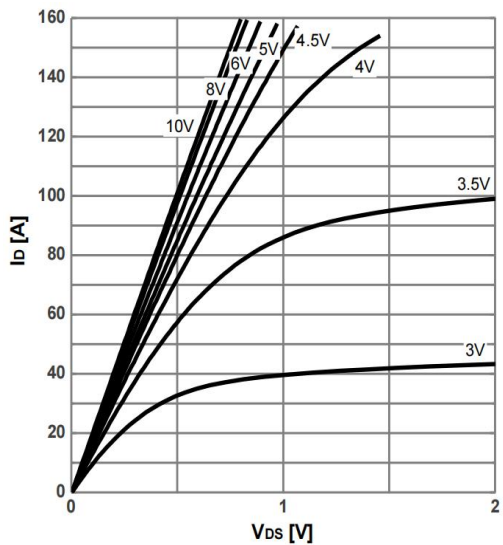
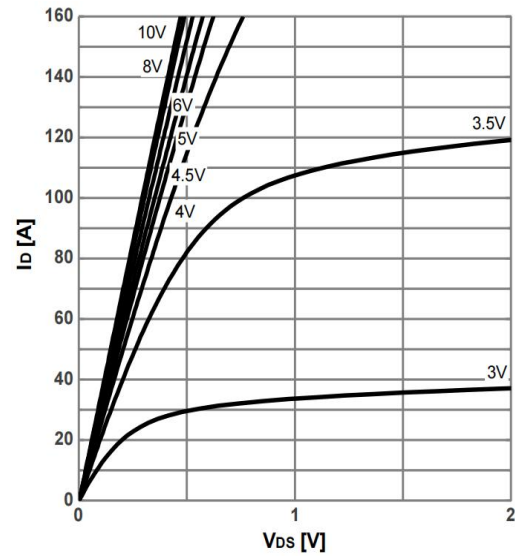
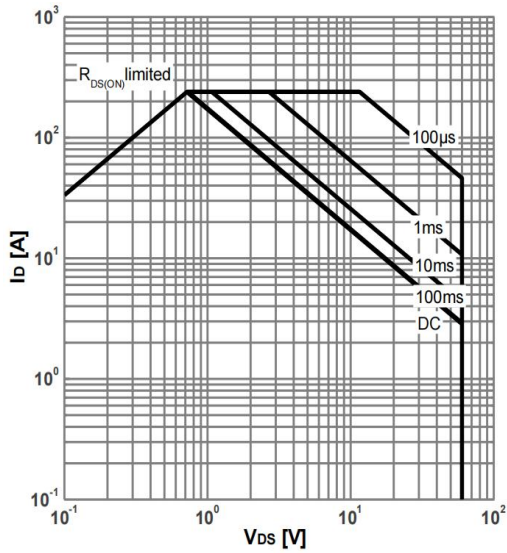
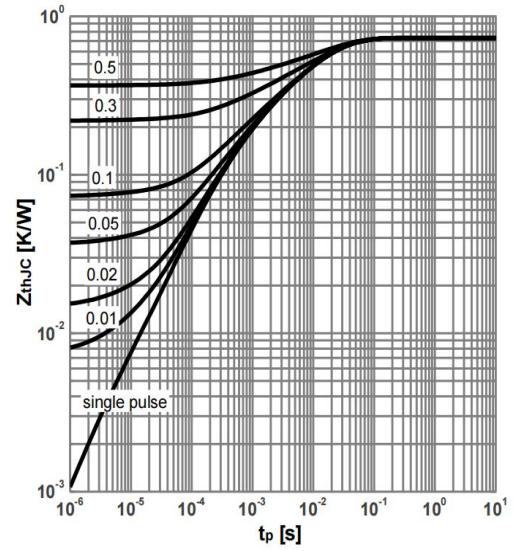
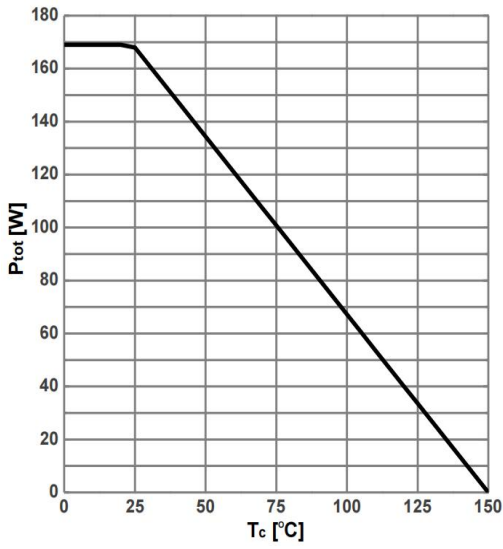
Note1:Pulse test: 300 μs pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

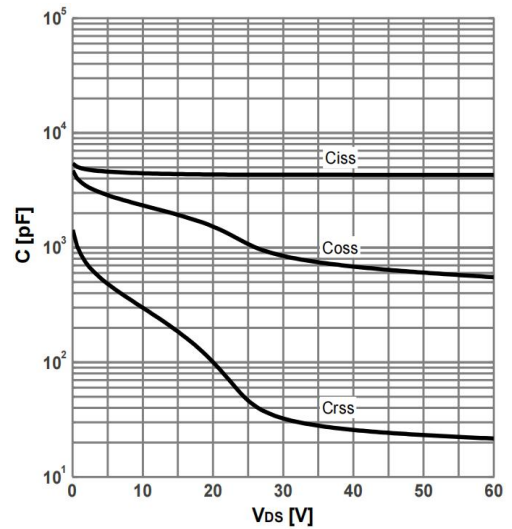
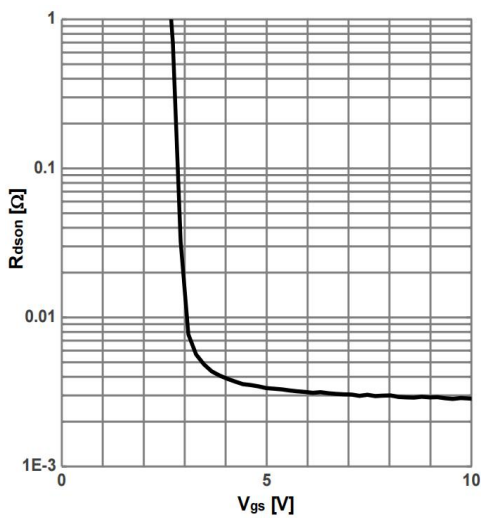
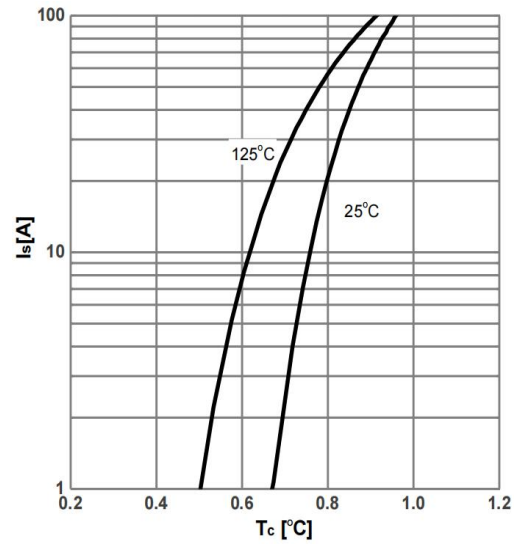
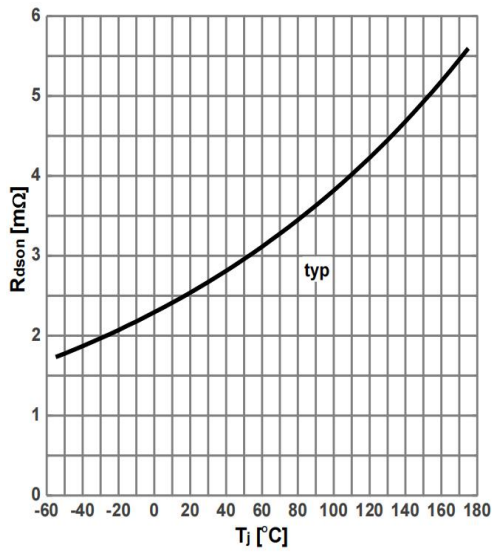
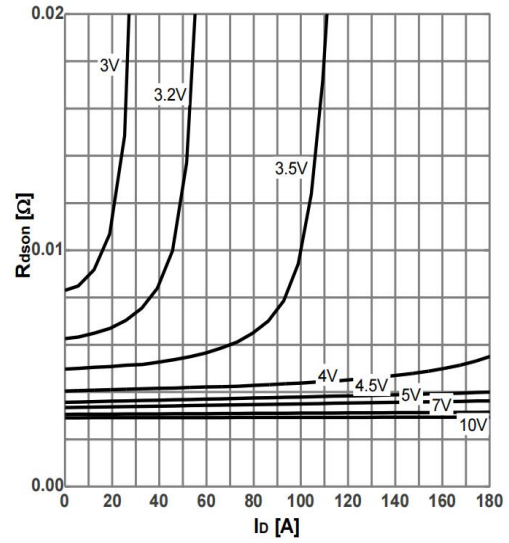
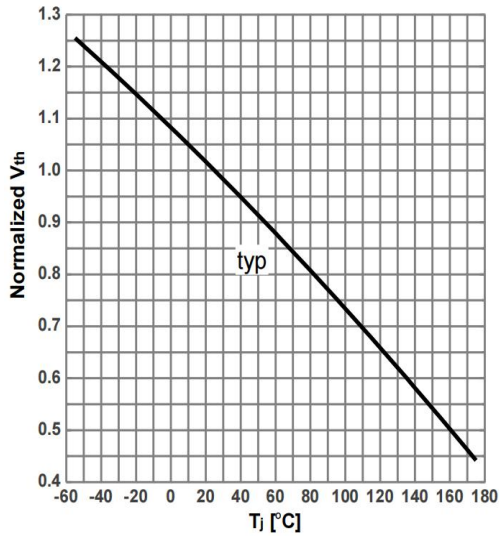
Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	BV_{DSS}	60	-	-	V
Drain-Source Leakage Current	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$	$R_{DS(on)}$	-	2.8	3	m Ω
Transconductance	$V_{DS}=5\text{V}, I_D=20\text{A}$	gfs		130		S
Input Capacitance	$V_{DS}=25\text{V}$ $V_{GS}=0\text{V}$ $f=1\text{MHz}$	C_{iss}	-	4200	-	pF
Output Capacitance		C_{oss}	-	1080	-	pF
Reverse Transfer Capacitance		C_{rss}	-	41	-	pF
Turn-on Delay Time(Note2)	$V_{DD}=30\text{V}$ $V_{GS}=10\text{V}$ $R_G=3\Omega$ $I_D=100\text{ A}$	$t_{d(ON)}$	-	13.5	-	ns
Rise Time(Note2)		t_r	-	95.5	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	40	-	ns
Fall Time(Note2)		t_f	-	110	-	ns
Total Gate Charge(Note2)	$V_{DS}=30\text{V}$ $V_{GS}=10\text{V}$ $I_D=20\text{A}$	Q_G	-	42	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	10	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	12	-	nC
Maximun Body-Diode Continuous Current		I_S	-	-	160	A
Drain-Source Diode Forward Voltage	$V_{GS}=0\text{V}, I_S=20\text{A}, T_J=25^\circ\text{C}$	V_{SD}	-	-	1.2	V
Reverse Recovery Time(Note2)	$T_J = 25^\circ\text{C}, I_F=60\text{A}$ $di / dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	35	-	ns
Reverse Recovery Charge(Note2)		Q_{rr}	-	30	-	nC

Note2:Pulse test: 300 μs pulse width, 2 % duty cycle

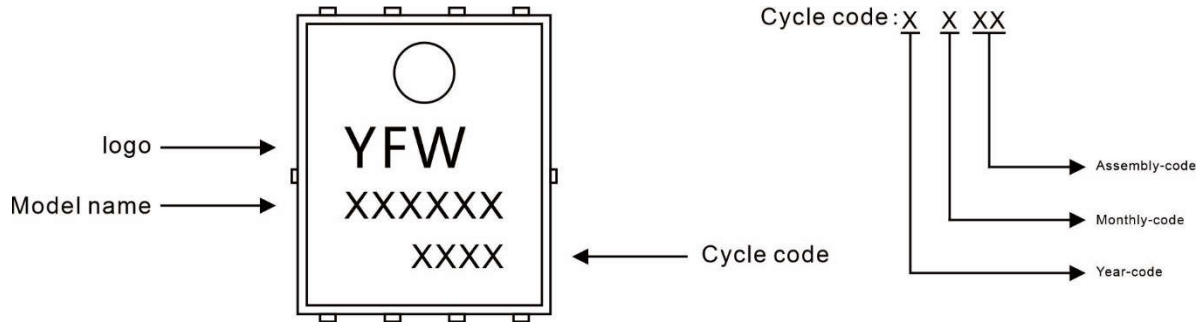
RATINGS AND CHARACTERISTIC CURVES



RATINGS AND CHARACTERISTIC CURVES



Marking Diagram



Ordering information

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
YFWG160N06NF	PDFN5*6-8L	0.0032oz(0.093g)	5000pcs/reel	10000pcs/box 50000pcs/Carton

Package Dimensions

PDFN5*6-8L

Dim	Millimeter		mil	
	Min.	Max.	Min.	Max.
A	0.9	1.2	35	45
A2	0.204	0.304	8	12
b	0.4ref.		16ref.	
b1	0.2	0.4	8	16
D	5.0	5.3	197	209
D1	4.84	5.24	191	206
E	5.95	6.35	234	250
E1	3.275	3.675	129	145
E2	5.69	6.09	224	232
e	1.27typ.		50typ.	
K	1.29typ.		51typ.	
L	0.585	0.785	23	27
L1	0.7typ.		28typ.	

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